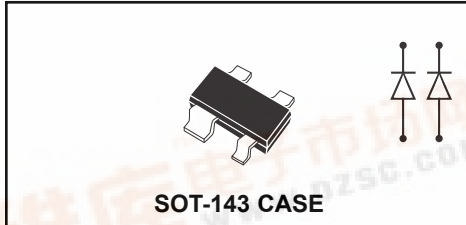


**CMFSH-3i**  
**DUAL, ISOLATED**  
**SILICON SCHOTTKY DIODES**



**SOT-143 CASE**

**MAXIMUM RATINGS:** ( $T_A=25\text{ }^\circ\text{C}$ )

Peak Repetitive Reverse Voltage  
 Continuous Forward Current  
 Peak Repetitive Forward Current  
 Forward Surge Current,  $t_p=10\text{ms}$   
 Power Dissipation  
 Operating and Storage  
 Junction Temperature  
 Thermal Resistance

SYMBOL		UNITS
$V_{RRM}$	30	V
$I_F$	100	mA
$I_{FRM}$	200	mA
$I_{FSM}$	750	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25\text{ }^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100\text{ }^\circ\text{C}$		25	100	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
$V_F$	$I_F=15\text{mA}$		0.40	0.45	V
$V_F$	$I_F=100\text{mA}$		0.74	1.00	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

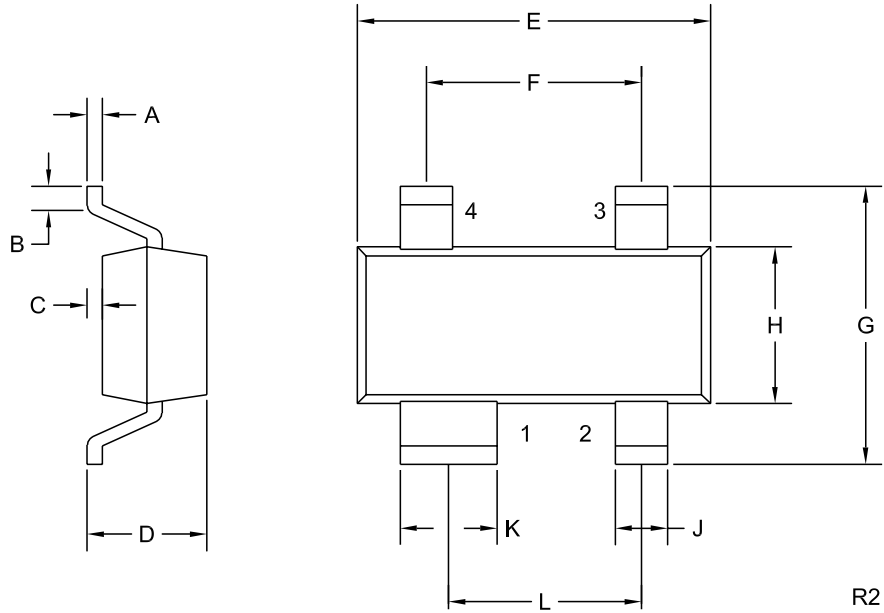
**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMFSH-3i consists of two electrically isolated silicon Schottky diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for fast switching applications requiring a low forward voltage drop.

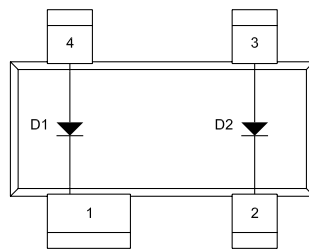
**MARKING CODE: C3I**



SOT-143 CASE - MECHANICAL OUTLINE



R2



**LEAD CODE:**

- 1) CATHODE D1
- 2) CATHODE D2
- 3) ANODE D2
- 4) ANODE D1

**MARKING CODE: C3I**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)